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TITLE: Etch apparatus for fabricating semiconductor

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PATENT-FAMILY:

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BASIC-ABSTRACT:

NOVELTY - An etch apparatus for fabricating a semiconductor is provided to compensate easily a temperature of a reaction chamber by using an end point detector window connected with a cable of a detector.

DETAILED DESCRIPTION - A heating portion(30) is installed in an end point detector window(12). The end point detector window(12) is connected with a cable(18) of a detector. The heating portion(30) is used for compensating a temperature in an etch process of a reaction chamber(10). The heating portion(30) has a heating line. The heating line of the heating portion(30) is wound between the end point detector window(12) and a housing(25) for forming a peripheral region of the end point detector window(12). A power supply portion is used for supplying power to the heating line. A control portion is connected with the power supply portion. The control portion is used for controlling the power supply portion and monitoring an internal temperature of the reaction chamber(10).

